

SRAM

512K x 8 SRAM

WITH OUTPUT ENABLE

FEATURES

- High speed: 20, 25, 35 and 55ns
- High-performance, low-power, CMOS double-metal process
- Single +5V ±10% power supply
- Easy memory expansion with \overline{CE} and \overline{OE} options
- All inputs and outputs are TTL compatible
- Fast \overline{OE} access time: 8ns

OPTIONS

- Timing
 - 20ns access
 - 25ns access
 - 35ns access
 - 55ns access

MARKING

- 20
- 25
- 35
- 55

- Packages
 - Plastic SOJ (400 mil)

DJ

NOTE: Available in ceramic packages tested to meet military specifications. Please refer to Micron's *Military Data Book*.

- 2V data retention

L

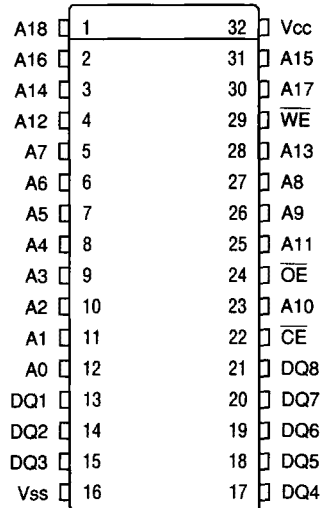
- Temperature

Industrial (-40°C to +85°C)	IT
Automotive (-40°C to +125°C)	AT
Extended (-55°C to +125°C)	XT

- Part Number Example: MT5C512K8A1DJ-25 L IT

PIN ASSIGNMENT (Top View)

32-Pin SOJ
(SD-5)



GENERAL DESCRIPTION

The Micron SRAM family employs high-speed, low-power CMOS designs using a four-transistor memory cell. Micron SRAMs are fabricated using double-layer metal, triple-layer polysilicon technology.

For flexibility in high-speed memory applications, Micron offers chip enable (\overline{CE}) capability. This enhancement can place the outputs in High-Z for additional flexibility in system design.

Writing to this device is accomplished when write enable (\overline{WE}) and \overline{CE} inputs are both LOW. Reading is accomplished when \overline{WE} remains HIGH while output enable (\overline{OE}) and \overline{CE} go LOW. The device offers a reduced power standby mode when disabled. This allows system designers to meet low standby power requirements.

All devices operate from a single +5V power supply and all inputs and outputs are fully TTL compatible.



MT5C512K8A1
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NEW

5 VOLT SRAM